

L Number	Hits	Search Text	DB	Time stamp
1	793	((("438/299") or ("438/301"))).CCLS.	USPAT	2002/01/25 14:15
2	498	((("257/410") or ("257/411"))).CCLS.	USPAT	2002/01/25 14:15
3	0	((("438/299") or ("438/301"))).CCLS.) and (SixOYNz)	USPAT	2002/01/25 14:15
4	1	((("438/299") or ("438/301"))).CCLS.) and (siliconoxynitride)	USPAT	2002/01/25 14:18
5	90	((("438/299") or ("438/301"))).CCLS.) and (silicon adj oxynitride)	USPAT	2002/01/25 14:26
6	27	((("438/299") or ("438/301"))).CCLS.) and (aluminum adj oxide)	USPAT	2002/01/25 14:19
7	4	((("5246883") or ("5250472") or ("5308793") or ("5573633"))).PN.	USPAT	2002/01/25 14:30
8	13	"5700349"	USPAT	2002/01/25 14:37
9	0	"5700349" and (dopant adj barrier)	USPAT	2002/01/25 14:37
10	1	((("438/299") or ("438/301"))).CCLS.) and (dopant adj barrier)	USPAT	2002/01/25 14:38
11	0	((("257/410") or ("257/411"))).CCLS.) and (dopant adj barrier)	USPAT	2002/01/25 14:38
12	324	(semiconductor) and substrate and transistor and ((silicon adj oxynitride) or (aluminum adj oxide) and BPSG and (silicon nitride)	USPAT	2002/01/25 15:41
15	0	(semiconductor) and substrate and transistor and ((silicon adj oxynitride) or (aluminum adj oxide) and BPSG and (silicon nitride)	JPO	2002/01/25 16:06
16	0	(semiconductor) and substrate and transistor and ((silicon adj oxynitride) or (aluminum adj oxide) and BPSG and (silicon nitride)	DERWENT	2002/01/25 15:42
17	0	(semiconductor) and substrate and transistor and ((silicon adj oxynitride) or (aluminum adj oxide) and BPSG and (silicon nitride)	IBM TDB	2002/01/25 15:42
14	1	(semiconductor) and substrate and transistor and ((silicon adj oxynitride) or (aluminum adj oxide) and BPSG and (silicon nitride)	EPO	2002/01/25 15:45
13	37	(aluminum adj oxide) and BPSG and (silicon nitride)	US-PGPUB	2002/01/25 15:49
18	0	(semiconductor) and substrate and transistor and ((silicon adj oxynitride) or (aluminum adj oxide) and BPSG and (silicon nitride)	US-PGPUB	2002/01/25 15:50
19	1	(semiconductor) and substrate and transistor and ((silicon adj oxynitride) or (aluminum adj oxide) and BPSG and (silicon nitride)	USPAT	2002/01/25 15:50
20	0	(semiconductor) and substrate and transistor and ((oxynitride) or (aluminum adj oxide) and BPSG and (silicon nitride)	JPO	2002/01/25 16:06
21	86442	438/\$.ccls. or 257/\$.ccls.	USPAT	2002/01/25 16:07
22	616	(438/\$.ccls. or 257/\$.ccls.) and ((("Si.sub.x O.sub.y N.sub.z" or "SiON" or "Al.sub.2 O.sub.3" or oxynitride or (aluminum adj oxide)) same (spacer spacers))	USPAT	2002/01/25 16:11
23	127	((("438/\$.ccls. or 257/\$.ccls.) and ((("Si.sub.x O.sub.y N.sub.z" or "SiON" or "Al.sub.2 O.sub.3" or oxynitride or (aluminum adj oxide)) same (spacer spacers))) and (BPSG or PSG or BSG or ASG)	USPAT	2002/01/25 16:12
24	4	"Al.sub.2 O.sub.3" or 257/\$.ccls.) and ((("Si.sub.x O.sub.y N.sub.z" or "SiON" or "Al.sub.2 O.sub.3" or oxynitride or (aluminum adj oxide)) same (spacer spacers))) and ((BPSG or PSG or BSG or ASG) and (dopant with barrier))	USPAT	2002/01/25 16:16
25	31	((("438/\$.ccls. or 257/\$.ccls.) and ((("Si.sub.x O.sub.y N.sub.z" or "SiON" or "Al.sub.2 O.sub.3" or oxynitride or (aluminum adj oxide)) same (spacer spacers))) and ((BPSG or PSG or BSG or ASG) and (dopant or diffusion) with barrier or prevent)))	USPAT	2002/01/25 16:22
26	67	(sidewall near2 (layers or multilayer)) and (transistor adj (gate or gates)) and (silicon near2 nitride) and semiconductor	USPAT	2002/01/25 16:31
28	682	((sidewall or spacer or sidewalls or spacers) near2 (layers or multilayer)) and (transistor or gate) and ((silicon near2 nitride) or (silicon adj oxynitride) or (aluminum adj oxide)) and semiconductor	USPAT	2002/01/25 16:35
27	155	((sidewall or spacer or sidewalls or spacers) near2 (layers or multilayer)) and (transistor adj (gate or gates)) and ((silicon near2 nitride) or (silicon adj oxynitride) or (aluminum adj oxide)) and semiconductor	USPAT	2002/01/25 16:35

29	632	((sidewall or spacer or sidewalls or spacers) near2 (layers or multilayer)) and (transistor or gate) and ((silicon near2 nitride) or (silicon adj oxynitride) or (aluminum adj oxide)) and semiconductor and (438/\$.ccls. or 257/\$.ccls.)	USPAT	2002/01/25 16:35
30	413	((sidewall or spacer or sidewalls or spacers) near2 (layers or multilayer)) and (transistor or gate) and ((silicon near2 nitride) or (silicon adj oxynitride) or (aluminum adj oxide)) and semiconductor and (438/\$.ccls. or 257/\$.ccls.) and ((sidewall or spacer or sidewalls or spacers) same ((silicon adj oxynitride) or (aluminum adj oxide) or (silicon adj nitride)))	USPAT	2002/01/25 16:38
31	7	((sidewall or spacer or sidewalls or spacers) near2 (layers or multilayer)) and (transistor or gate) and ((silicon near2 nitride) or (silicon adj oxynitride) or (aluminum adj oxide)) and semiconductor and (438/\$.ccls. or 257/\$.ccls.) and ((sidewall or spacer or sidewalls or spacers) same ((silicon adj oxynitride) or (aluminum adj oxide) or (silicon adj nitride))) and ((first adj (spacer or spacers or sidewall or sidewall)) near4 ((silicon adj oxynitride) or (aluminum adj oxide) or (silicon adj nitride)))	USPAT	2002/01/25 16:40